



Product Summary

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.



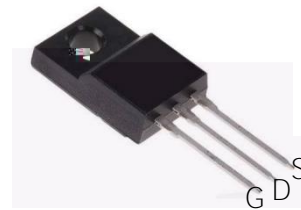
$V_{DS} = 80V$

$R_{DS(ON)} = 8.8m$

$I_D = 45A$

Trench technology
 $R_{DS(ON)}$ to minimize conductive loss

nd Synchronous Rectifier



TO-220F

Part NO.	ZM100N08HF
Marking	ZM100N08H
Packing Information	Bulk Tube
Basic ordering unit (pcs)	1000

$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current	$I_{D@TC=25}$	45	A
	$I_{D@TC=75}$	34	A
	$I_{D@TC=100}$	28	A
Pulsed Drain Current	I_{DM}	135	A
Total Power Dissipation($TC=25$)	$P_D@TC=25$	75	W
Total Power Dissipation($TA=25$)	$P_D@TA=25$	2	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	



Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
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Fig.7 On-Resistance VS Gate Source Voltage

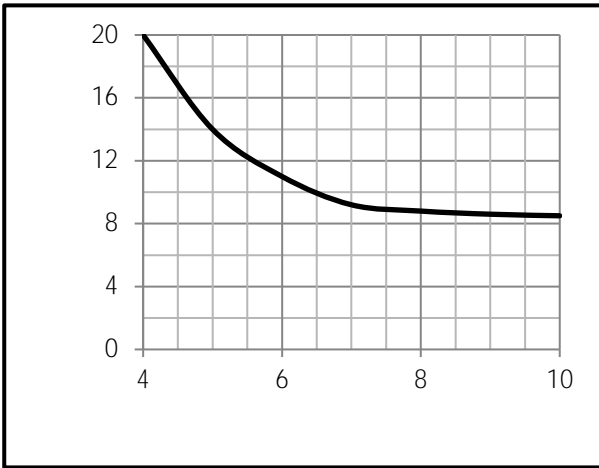


Fig.8 On-Resistance V.S Junction Temperature

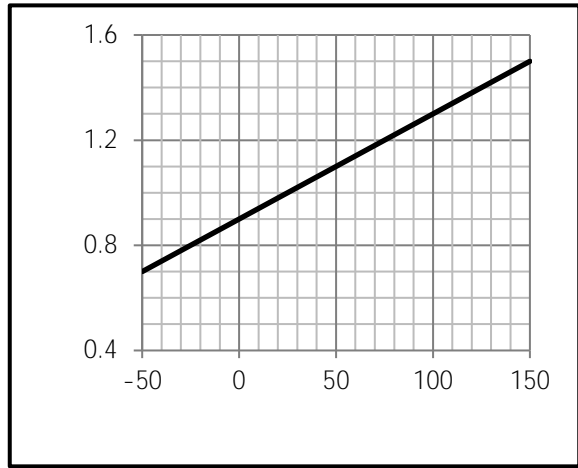


Fig.9 Switching Time Measurement Circuit

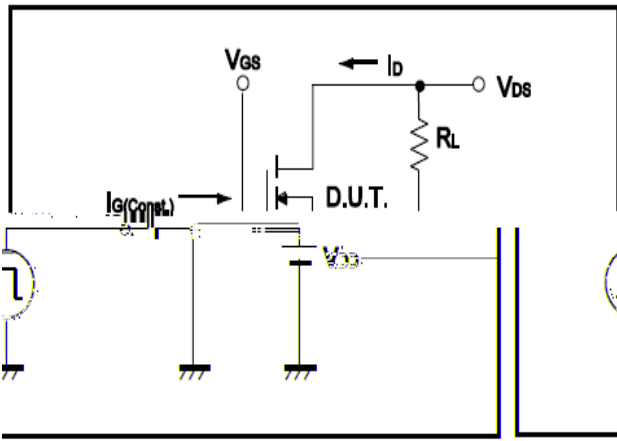


Fig.10 Gate Charge Waveform

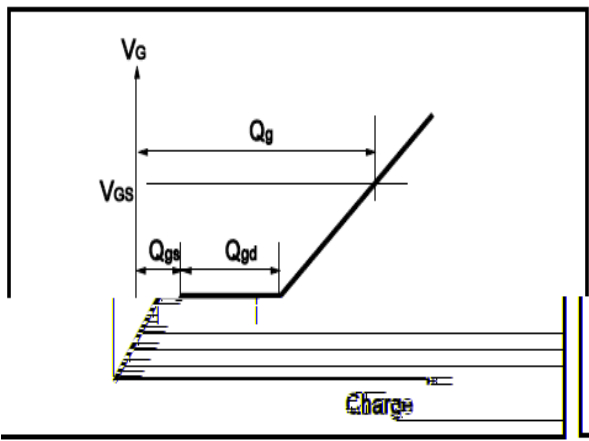


Fig.11 Switching Time Measurement Circuit

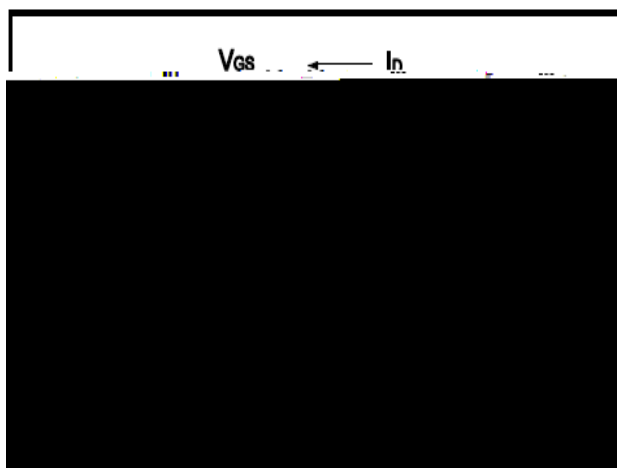


Fig.12 Gate Charge Waveform

